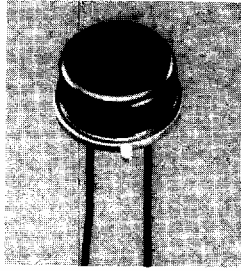
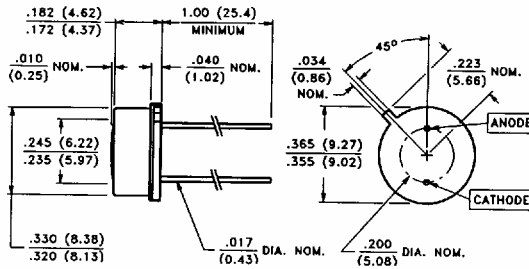


E G & G VACTEC



PACKAGE DIMENSIONS Inch (mm)



PRODUCT DESCRIPTION

Planar silicon photodiode in a "flat" window, dual lead TO-5 package. The package incorporates an infrared rejection filter. Cathode is common to the case. These diodes have very high shunt resistance and good blue response.

CASE 14 TO-5 HERMETIC
CHIP ACTIVE AREA: .008 in² (5.16 mm²)

ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -40°C to 110°C
Operating Temperature: -40°C to 110°C

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTB curves, pages 12-13)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTB5040B			VTB5041B			UNITS		
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.
I _{sc}	Short Circuit Current	H = 100 fc, 2850 K	3.0	4.5		3.0	4.5				μA
TC I _{sc}	I _{sc} Temp. Coefficient	2850 K		.02	.08		.02	.08			% / °C
V _{oc}	Open Circuit Voltage	H = 100 fc, 2850 K		420			420				mV
TC V _{oc}	V _{oc} Temp. Coefficient	2850 K		-2.0			-2.0				mV / °C
I _d	Dark Current	H = 0, V _R = 2.0 V			2000			100			pA
R _{SH}	Shunt Resistance	H = 0, V = 10 mV		.07			1.4				GΩ
TC R _{SH}	R _{SH} Temp. Coefficient	H = 0, V = 10 mV		-8.0			-8.0				% / °C
C _J	Junction Capacitance	H = 0, V = 0		1.0			1.0				nF
λ _{range}	Spectral Application Range		330		720	330		720			nm
λ _p	Spectral Response - Peak			580			580				nm
V _{BR}	Breakdown Voltage		2	40		2	40				V
θ _{1/2}	Ang. Resp. - 50% Resp. Pt.			±45			±45				Degrees
NEP	Noise Equivalent Power			1.1 x 10 ⁻¹³ (Typ.)			2.4 x 10 ⁻¹⁴ (Typ.)				W/√Hz
D*	Specific Detectivity			2.2 x 10 ¹² (Typ.)			9.7 x 10 ¹² (Typ.)				cm ² /Hz/W